

HD74HC243

Quad. Bus Transceivers (with noninverted 3-state outputs)

REJ03D0596-0200
 (Previous ADE-205-473)
 Rev.2.00
 Jan 31, 2006

Description

The HD74HC243 is a noninverting buffer. Each device has one active high enable (GBA), and one active low enable ($\overline{\text{GAB}}$). GBA enables the A output and $\overline{\text{GAB}}$ enables the B outputs. The device does not have schmitt trigger inputs.

Features

- High Speed Operation: $t_{pd} = 10 \text{ ns typ (} C_L = 50 \text{ pF)}$
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2 \text{ to } 6 \text{ V}$
- Low Input Current: $1 \mu\text{A max}$
- Low Quiescent Supply Current: $I_{CC} \text{ (static)} = 4 \mu\text{A max (} T_a = 25^\circ\text{C)}$
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74HC243P	DILP-14 pin	PRDP0014AB-B (DP-14AV)	P	—
HD74HC243FPEL	SOP-14 pin (JEITA)	PRSP0014DF-B (FP-14DAV)	FP	EL (2,000 pcs/reel)

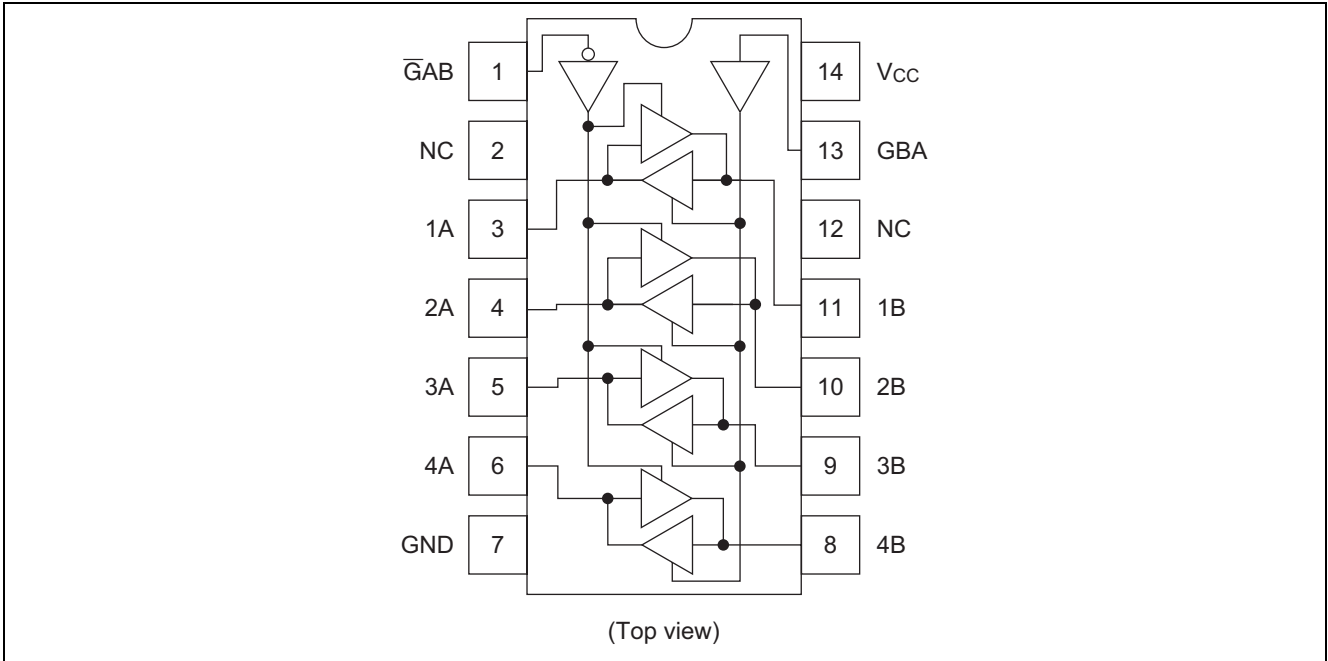
Note: Please consult the sales office for the above package availability.

Function Table

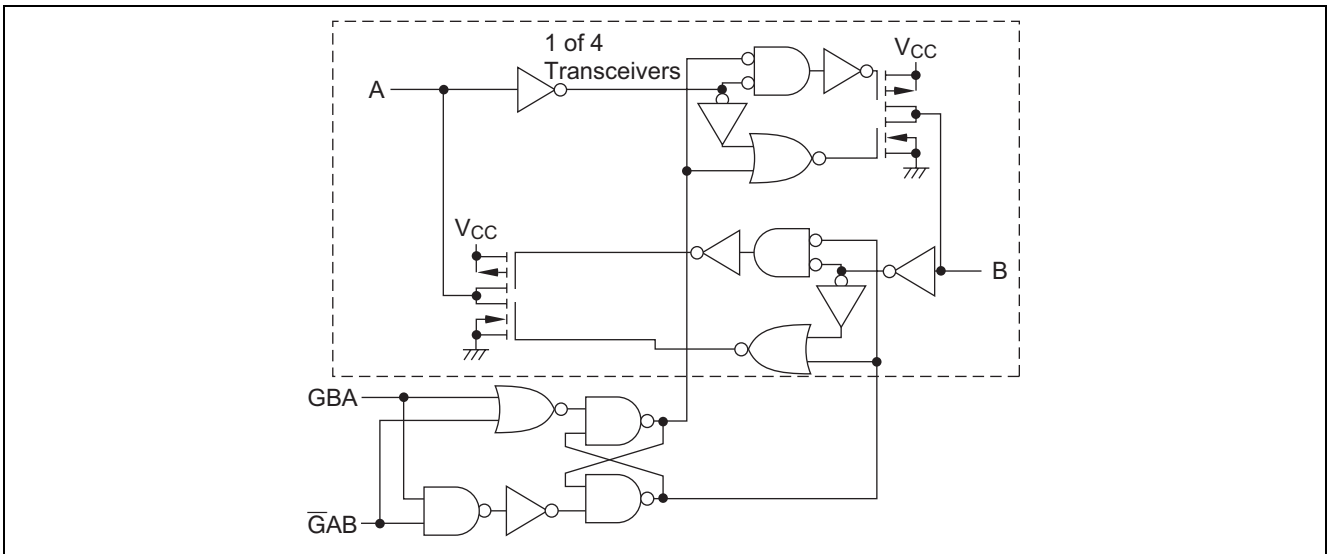
Control Inputs		Data Port Status	
$\overline{\text{GAB}}$	GBA	A	B
H	H	O	I
L	H	Z	Z
H	L	Z	Z
L	L	I	O

H : high level
 L : low level
 X : irrelevant
 I : input
 O : output
 Z : high-impedance

Pin Arrangement



Logic Diagram



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit
Supply voltage range	V_{CC}	-0.5 to 7.0	V
Input / Output voltage	V_{IN}, V_{OUT}	-0.5 to $V_{CC} + 0.5$	V
Input / Output diode current	I_{IK}, I_{OK}	± 20	mA
Output current	I_O	± 35	mA
V_{CC} , GND current	I_{CC} or I_{GND}	± 75	mA
Power dissipation	P_T	500	mW
Storage temperature	T_{stg}	-65 to +150	°C

Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V_{CC}	2 to 6	V	
Input / Output voltage	V_{IN}, V_{OUT}	0 to V_{CC}	V	
Operating temperature	T_a	-40 to 85	°C	
Input rise / fall time ^{*1}	t_r, t_f	0 to 1000	ns	$V_{CC} = 2.0\text{ V}$
		0 to 500		$V_{CC} = 4.5\text{ V}$
		0 to 400		$V_{CC} = 6.0\text{ V}$

Notes: 1. This item guarantees maximum limit when one input switches.
Waveform: Refer to test circuit of switching characteristics.

Electrical Characteristics

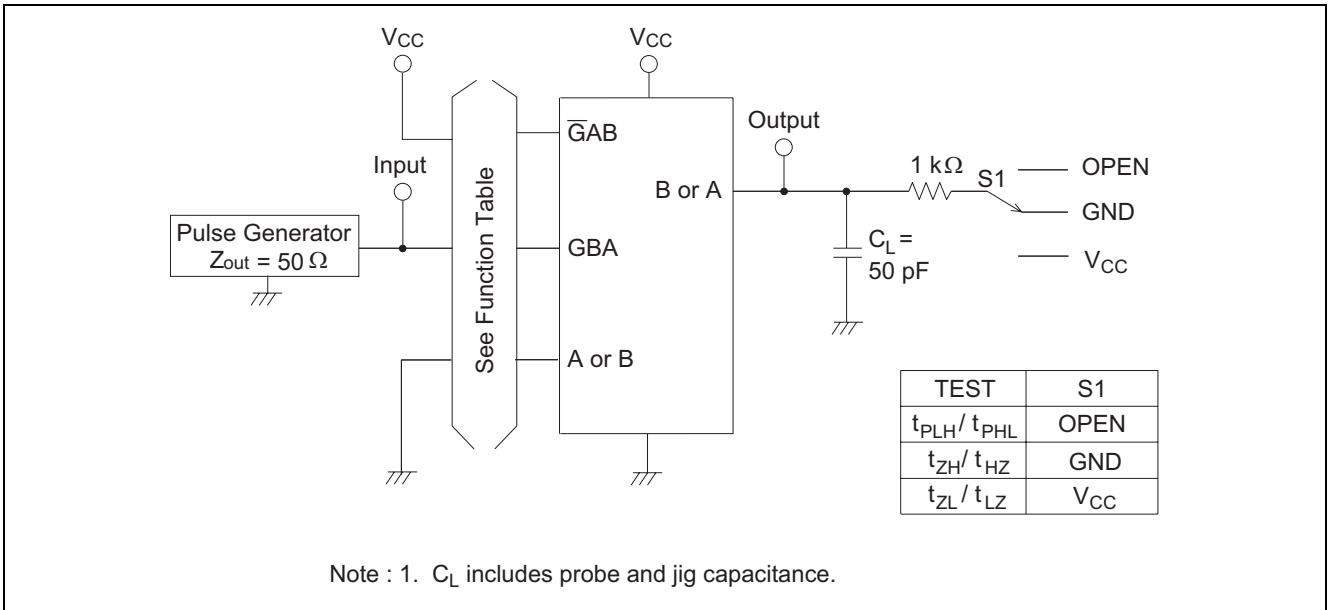
Item	Symbol	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40\text{ to }+85^\circ\text{C}$		Unit	Test Conditions	
			Min	Typ	Max	Min	Max			
Input voltage	V_{IH}	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V_{IL}	2.0	—	—	0.5	—	0.5	V		
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V_{OH}	2.0	1.9	2.0	—	1.9	—	V	$V_{in} = V_{IH}$ or V_{IL}	$I_{OH} = -20\ \mu\text{A}$
		4.5	4.4	4.5	—	4.4	—			$I_{OH} = -6\ \text{mA}$
		6.0	5.9	6.0	—	5.9	—			$I_{OH} = -7.8\ \text{mA}$
		4.5	4.18	—	—	4.13	—			
		6.0	5.68	—	—	5.63	—			
	V_{OL}	2.0	—	0.0	0.1	—	0.1	V	$V_{in} = V_{IH}$ or V_{IL}	$I_{OL} = 20\ \mu\text{A}$
		4.5	—	0.0	0.1	—	0.1			
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33			$I_{OL} = 6\ \text{mA}$
		6.0	—	—	0.26	—	0.33			$I_{OL} = 7.8\ \text{mA}$
Off-state output current	I_{OZ}	6.0	—	—	± 0.5	—	± 5.0	μA	$V_{in} = V_{IH}$ or V_{IL} , $V_{out} = V_{CC}$ or GND	
Input current	I_{in}	6.0	—	—	± 0.1	—	± 1.0	μA	$V_{in} = V_{CC}$ or GND	
Quiescent supply current	I_{CC}	6.0	—	—	4.0	—	40	μA	$V_{in} = V_{CC}$ or GND, $I_{out} = 0\ \mu\text{A}$	

Switching Characteristics

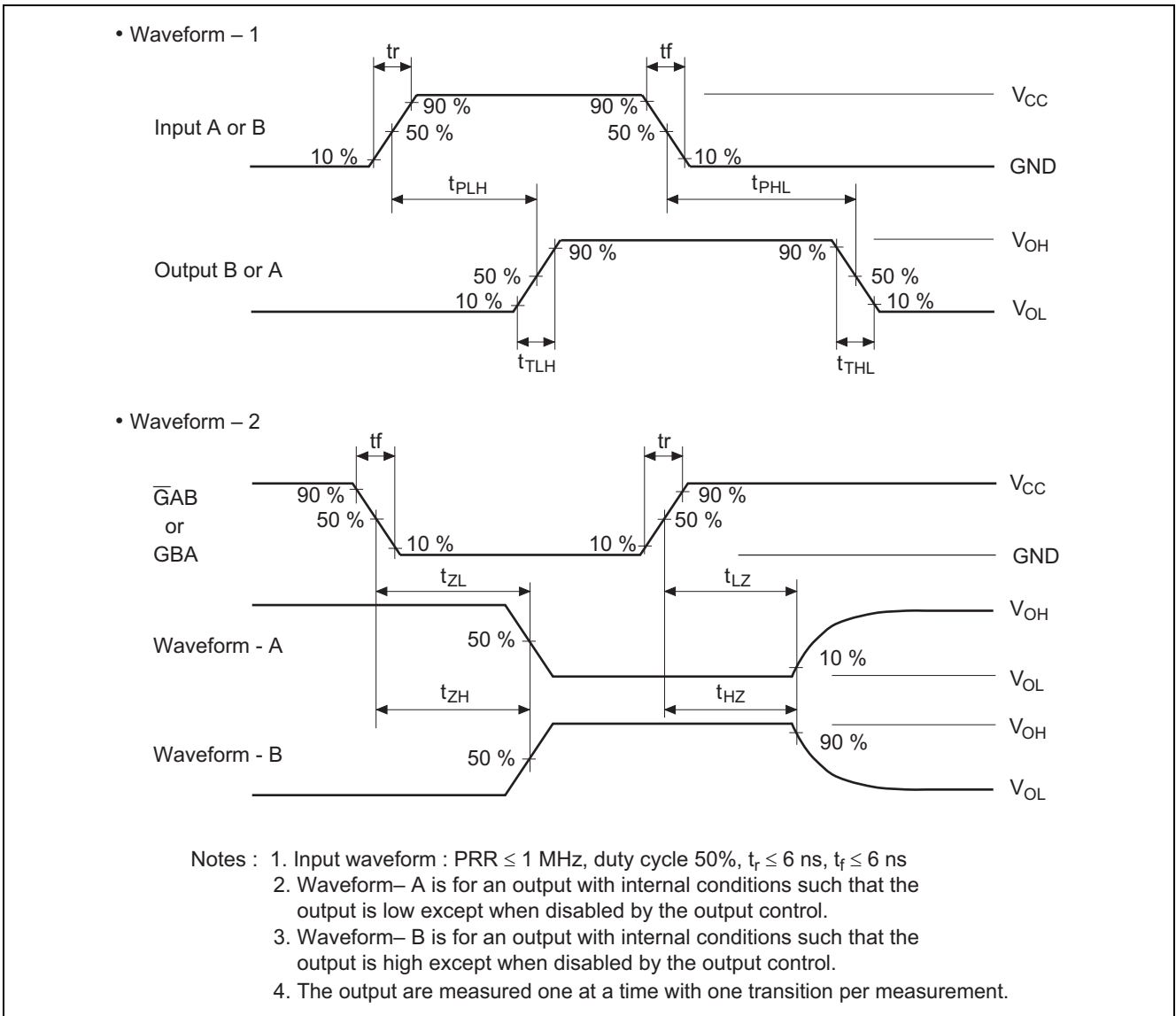
($C_L = 50$ pF, Input $t_r = t_f = 6$ ns)

Item	Symbol	V _{CC} (V)	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions
			Min	Typ	Max	Min	Max		
Propagation delay time	t _{PHL}	2.0	—	—	90	—	115	ns	
		4.5	—	10	18	—	23		
		6.0	—	—	15	—	20		
	t _{PLH}	2.0	—	—	90	—	115	ns	
		4.5	—	10	18	—	23		
		6.0	—	—	15	—	20		
Output enable time	t _{ZL}	2.0	—	—	150	—	190	ns	
		4.5	—	14	30	—	38		
		6.0	—	—	26	—	33		
	t _{ZH}	2.0	—	—	150	—	190	ns	
		4.5	—	15	30	—	38		
		6.0	—	—	26	—	33		
Output disable time	t _{LZ}	2.0	—	—	150	—	190	ns	
		4.5	—	18	30	—	38		
		6.0	—	—	26	—	33		
	t _{HZ}	2.0	—	—	150	—	190	ns	
		4.5	—	20	30	—	38		
		6.0	—	—	26	—	33		
Output rise/fall time	t _{TLH}	2.0	—	—	60	—	75	ns	
	t _{THL}	4.5	—	4	12	—	15		
	t _{THL}	6.0	—	—	10	—	13		
Input capacitance	C _{in}	—	—	5	10	—	10	pF	

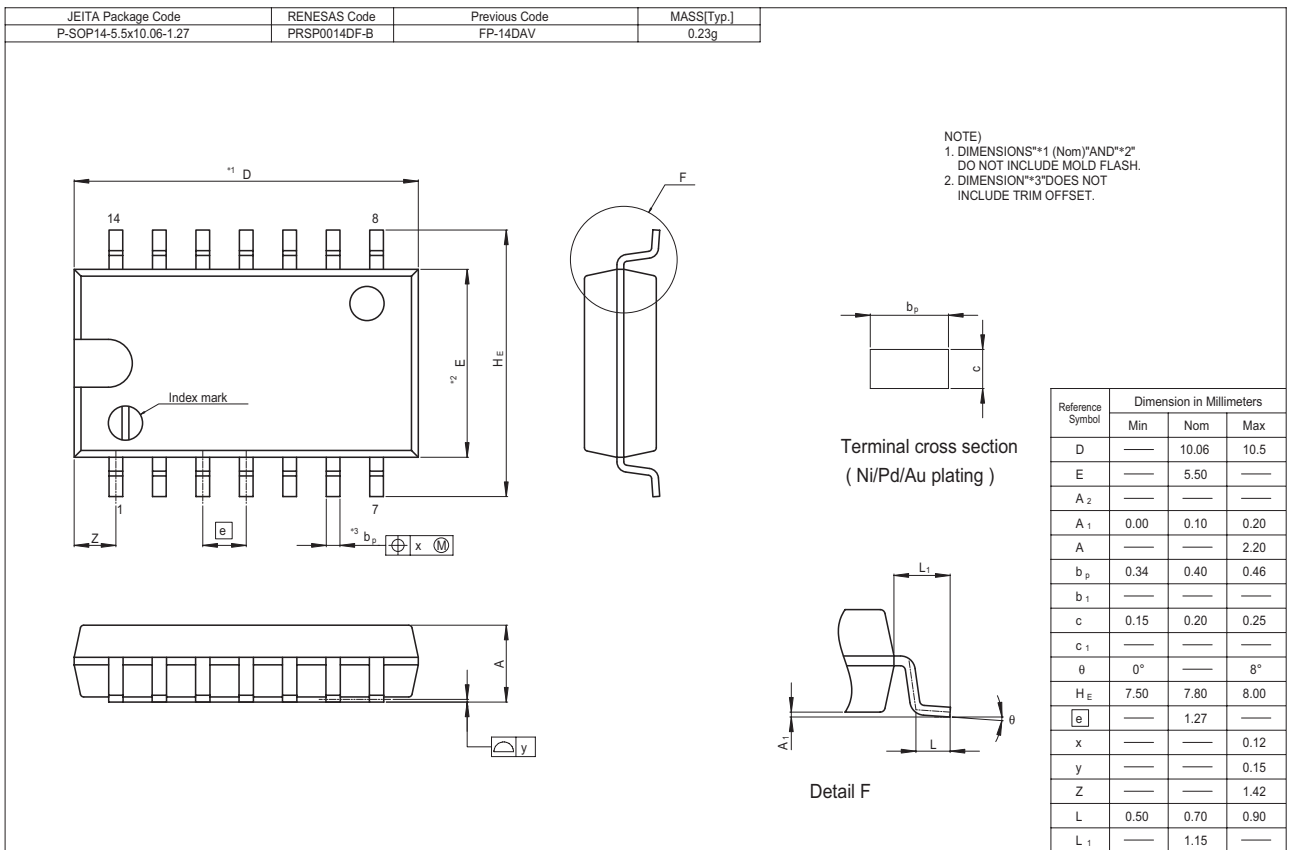
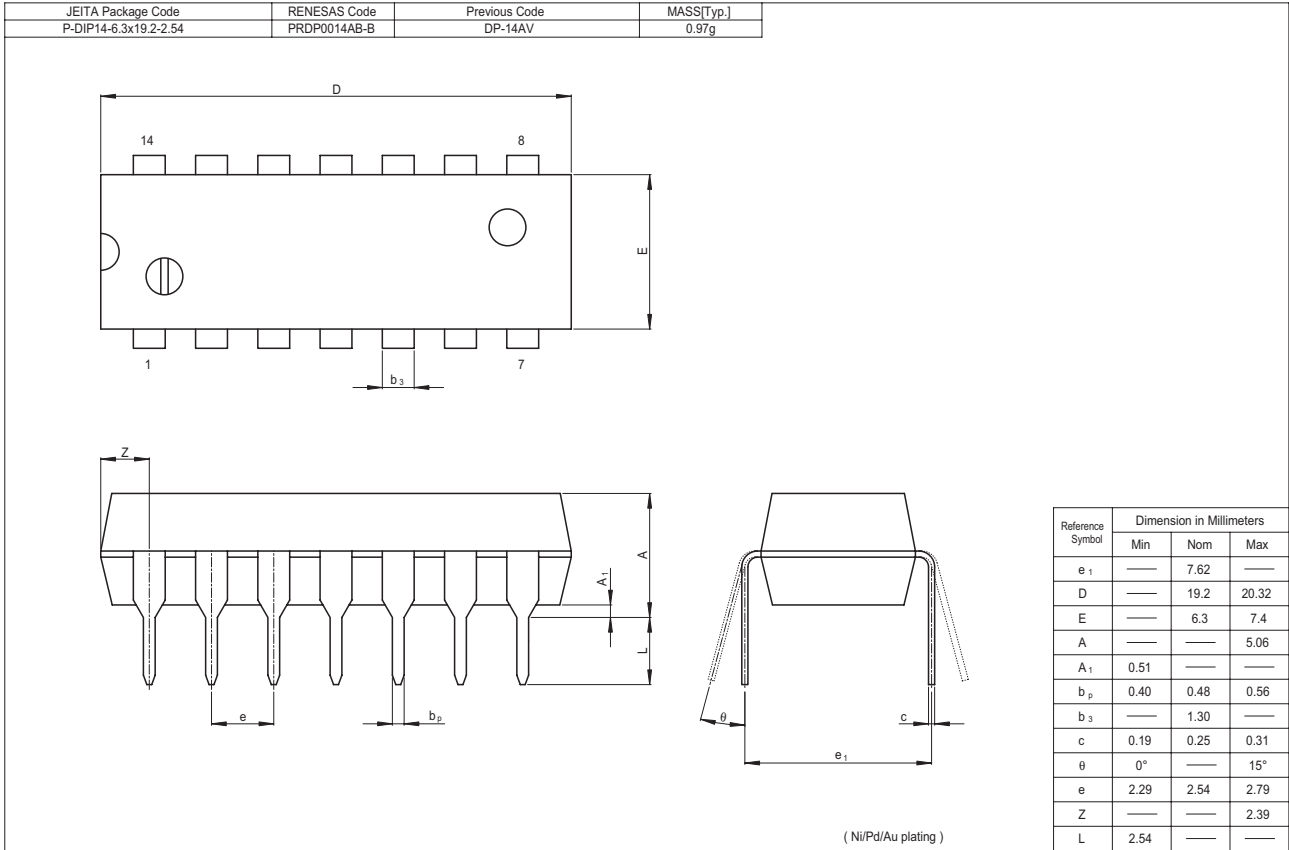
Test Circuit



Waveforms



Package Dimensions



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